

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

Claims 1-13 (Canceled).

14. (Original) An exposure data creating method comprising:
dividing layout data of a semiconductor apparatus into sizes of basic figure apertures which take reduction in exposure into consideration;
classifying the divided layouts according to the basic figure apertures; and
creating first data which prevent a beam emitted onto overlapped portions of the divided layouts and the basic figure apertures from being deflected.

15. (Currently Amended) The exposure data creating method as in claim 14, further comprising:

creating second data ~~comprises~~ including
positions of the divided layouts in the layout of the semiconductor apparatus;

names of the classified basic figures; and
addresses to be capable of reading the first data,
wherein the positions, the names and the addresses have correspondence to one another.

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16. (Original) An exposure data creating method comprising:
 - dividing chip data into units or sizes of standard cell patterns;
 - classifying the divided chip data according to the standard cell patterns in library; and
 - obtaining overlapped portions of the divided chip data and the classified standard cell patterns so as to create data which shows existence/non-existence of deflection of a beam on a blanking aperture array.

17. (Original) An exposure data creating method comprising:
 - dividing layout data of a semiconductor apparatus into vertical line patterns and horizontal line patterns which take reduction in exposure into consideration;
 - thickening widths of the vertical line patterns so as to create a first pattern where the adjacent vertical line patterns are integrated;
 - thickening widths of the horizontal line patterns so as to create a second pattern where the adjacent horizontal line patterns are integrated;
 - dividing the first and second patterns into sizes of basic figure apertures which take reduction in exposure into consideration;
 - classifying the divided first and second patterns according to the basic figure apertures; and

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obtaining overlapped portions of the divided first and second patterns and the classified basic figure apertures so as to create first data which show existence/non-existence of deflection for each aperture sections on an aperture array.

18. (Currently Amended) The exposure data creating method as in claim 17, further comprising:

creating second data comprises including
positions of the divided first and second patterns in the layout of the semiconductor apparatus;
names of the classified basic figures; and
addresses to be capable of reading the first data,
wherein the positions, the names and the addresses have correspondence to one another.

19. (Original) A recording medium to record exposure data being capable of being read by a computer, the exposure data comprising:

first data to prevent a beam emitted to overlapped portions of layout data of a semiconductor apparatus, which are divided into sizes of basic figure apertures which take reduction in exposure into consideration, and the basic figure apertures for classifying divided layouts from being deflected.

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20. (Original) The recording medium for recording exposure data being capable of being read by a computer as in claim 19, the exposure data further comprising:

second data which have positions of the divided layouts in the layout of the semiconductor apparatus, names of the classified basic figure apertures and addresses for being capable of reading said first data, and in which the positions and the names and the addresses have correspondence to one another.

21. (Original) A recording medium for recording a program for creating exposure data thereinto being capable of being read by a computer, the program comprising:

dividing layout data of a semiconductor apparatus into sizes of basic figure apertures which take reduction in exposure into consideration;

classifying the divided layouts according to the basic figure apertures; and
obtaining overlapped portions of the divided layouts and the classified basic figure apertures so as to create first data which shows existence/non-existence of deflection at aperture sections of an aperture array.

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22. (Currently Amended) The recording medium for recording a program for creating exposure data capable of being read by a computer as in claim 21, the program further comprising:

creating second data comprises including
positions of the divided layouts in the layout of the semiconductor apparatus;
names of the classified basic figures; and
addresses to be capable of reading the first data,
wherein the positions, the names and the addresses have correspondence to one another.

23. (Original) A charged beam exposure method comprising:
dividing layout data of a semiconductor apparatus into sizes of basic figure apertures which take reduction in exposure into consideration;
classifying the divided layouts according to the basic figure apertures; and
emitting a beam onto a sample, the beam being shaped into a form of an overlapped portion of the divided layouts and the classified basic figure apertures.

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24. (Original) The charged beam exposure method as in claim 23, wherein said emitting onto the sample comprises

obtaining the overlapped portion of the divided layouts and the classified basic figure apertures so as to create first data which shows existence/non-existence of deflection at aperture sections on a blanking aperture array.

25. (Original) The charged beam exposure method as in claim 24, wherein said emitting onto the sample comprises

creating second data which have positions of the divided layouts in the layout of the semiconductor apparatus, names of the classified basic figures, and in which the positions and the names and the addresses have correspondence to one another.

26. (Original) The charged beam exposure method as in claim 25, wherein said emitting onto the sample comprises:

calling the position;
calling the name and the address of the basic figures which have correspondence to the called position; and
calling the first data from the address.

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27. (Original) The charged beam exposure method as in claim 26, wherein said emitting onto the sample comprises:

applying a voltage for deflection control to electrodes of blanking aperture array based on the first data;

applying a control voltage to a deflector for basic figure selection based on the name of the basic figure; and

applying a control voltage to a deflector for position specifying based on the position.

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